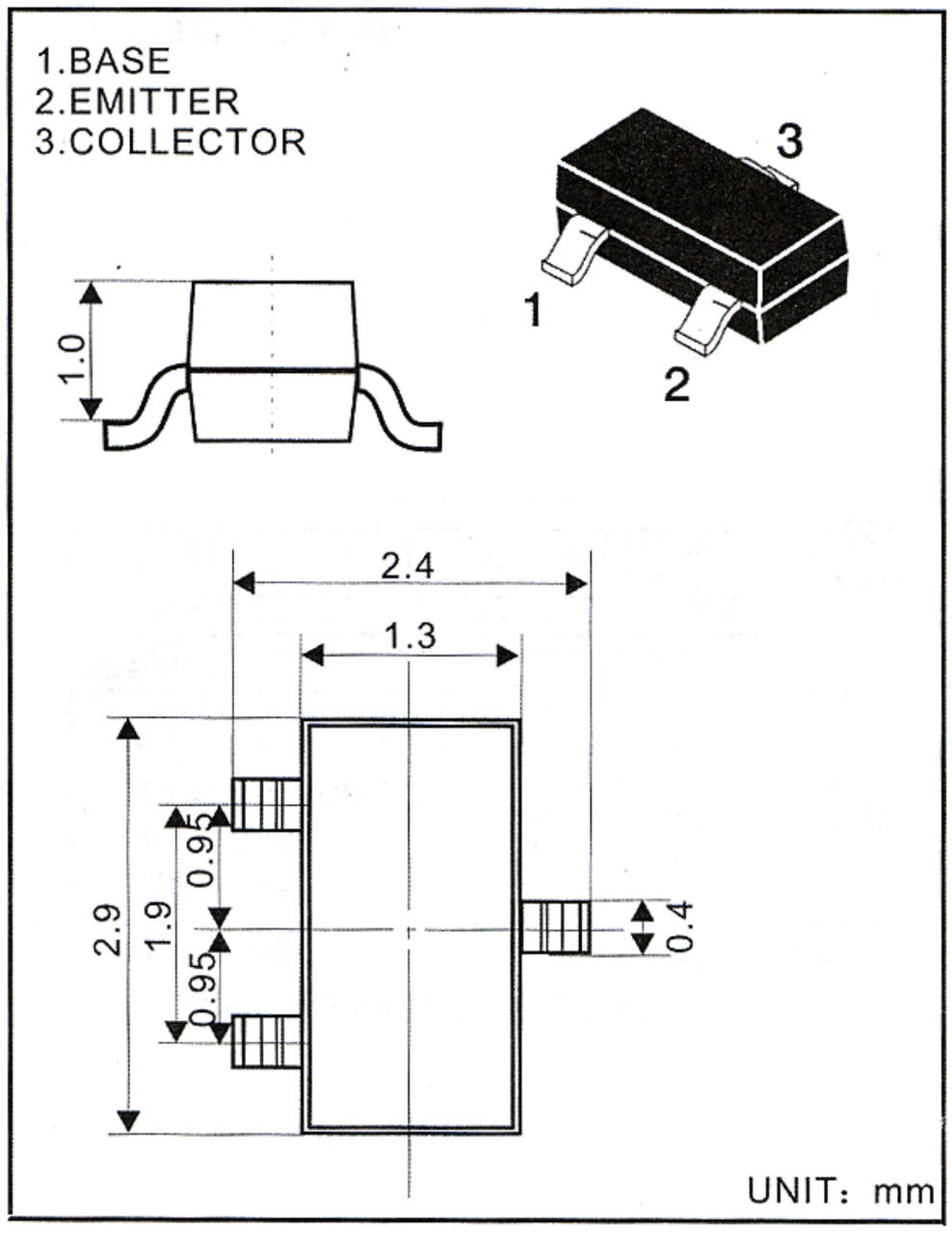
SOT-23 Plastic-Encapsulate Transistors

A1015LT1 TRANSISTOR (PNP)



FEATURES

Power dissipation

PCM：0.2 W（Tamb=25℃）

Collector current

ICM：-0.15 A

Collector-base voltage

V(BR)CBO: -50V

Operating and storage junction temperature range

TJ,Tstg : -55℃ to+150℃

ELECTRICAL CHARACTERISTICS

(Tamp=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=-100μA, IE=0	-50			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=-0.1mA, IB=0	-50			V
Collector cut-off current	ICBO	VCB=-50V,IE=0			-0.1	μA
Emitter cut-off current	IEBO	VEB=-5V, IC=0			-0.1	μA
DC current gain	HFE	VCE=-6V, IC=-2mA	130		400	
Collector-emitter saturation voltage	VCEsat	IC=-100mA,IB=-10mA			-0.3	V
Base-emitter saturation voltage	VBEsat	IC=-100mA,IB=-10mA			-1.1	V
Base-emitter voltage	VBEF	IE=-310mA			-1.45	V
Transition frequency	fT	VCE=-10V,IC=-1mA,f=30MHz	80			MHz

CLASSIFICATION OF hFE

Rank	L	H
Range	130-200	200-400

DEVICE MARKING : A1015LT1=BA

Typical Characteristics